#### 查询SN74HC20供应商

## 捷多邦,专业PCB打样工厂, SN54月6205 SN74HC20 **DUAL 4-INPUT POSITIVE-NAND GATES**

SN54HC20 ... J OR W PACKAGE

SCLS086D - DECEMBER 1982 - REVISED FEBRUARY 2000

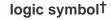
Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Standard Plastic (N) and Ceramic (J) DIPs

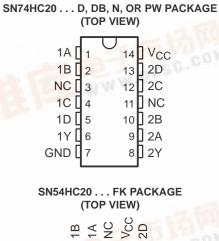
## description

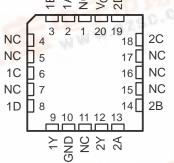
The 'HC20 devices contain two independent 4-input NAND gates. They perform the Boolean function  $Y = \overline{A \bullet B \bullet C \bullet D}$  or  $Y = \overline{A} + \overline{B} + \overline{C} + \overline{D}$  in positive logic.

The SN54HC20 is characterized for operation over the full military temperature range of -55°C to 125°C. The SN74HC20 is characterized for operation from -40°C to 85°C.

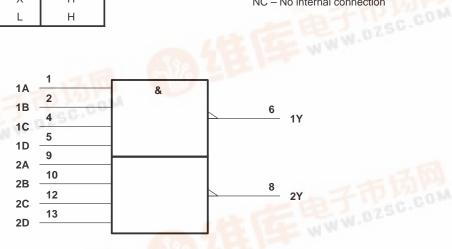
	FU	NCTION (each g		-
	INP	UTS	13	OUTPUT
Α	В	С	D	YC
Н	Н	Н	н	Dec. F
L	Х	Х	Х	н
х	L	Х	Х	н
Х	Х	L	Х	н
Х	Х	Х	L	н







NC - No internal connection



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the D, DB, J, N, PW, and W packages. WWW.DZSC.COM



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## logic diagram (positive logic)



Pin numbers shown are for the D, DB, J, N, PW, and W packages.

## absolute maximum ratings over operating free-air temperature range<sup>†</sup>

Supply voltage range, V <sub>CC</sub>		. $-0.5$ V to 7 V
Input clamp current, $I_{IK}$ (V <sub>I</sub> < 0 or V <sub>I</sub> > V <sub>CC</sub> ) (see	e Note 1)	±20 mA
Output clamp current, $I_{OK}$ (V <sub>O</sub> < 0 or V <sub>O</sub> > V <sub>CC</sub>	(see Note 1)	±20 mA
Continuous output current, $I_O (V_O = 0 \text{ to } V_{CC})$	• • • • • • • • • • • • • • • • • • • •	±25 mA
Continuous current through V <sub>CC</sub> or GND		±50 mA
Package thermal impedance, $\theta_{JA}$ (see Note 2):		
	DB package	96°C/W
	N package	80°C/W
	PW package	113°C/W
Storage temperature range, T <sub>stg</sub>		–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

2. The package thermal impedance is calculated in accordance with JESD 51.

#### recommended operating conditions (see Note 3)

			S	SN54HC20			SN74HC20		
			MIN	NOM	MAX	MIN	NOM	MAX	UNIT
VCC	Supply voltage		2	5	6	2	5	6	V
		$V_{CC} = 2 V$	1.5			1.5			
$V_{\text{IH}}$	High-level input voltage	$V_{CC} = 4.5 V$	3.15			3.15			V
		$V_{CC} = 6 V$	4.2			4.2			
		$V_{CC} = 2 V$	0		0.5	0		0.5	
VIL	Low-level input voltage	$V_{CC} = 4.5 V$	0		1.35	0		1.35	V
		$V_{CC} = 6 V$	0		1.8	0		1.8	
VI	Input voltage		0		VCC	0		VCC	V
VO	Output voltage		0		VCC	0		VCC	V
t <sub>t</sub> Input transi		$V_{CC} = 2 V$	0		1000	0		1000	
	Input transition (rise and fall) time	$V_{CC} = 4.5 V$	0		500	0		500	ns
		$V_{CC} = 6 V$	0		400	0		400	
TA	Operating free-air temperature		-55		125	-40		85	°C

NOTE 3: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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PARAMETER	TEST CONDITIONS		м	T <sub>A</sub> = 25°C			SN54HC20		SN74HC20		
PARAMETER			Vcc	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
			2 V	1.9	1.998		1.9		1.9		V
		I <sub>OH</sub> = -20 μA	4.5 V	4.4	4.499		4.4		4.4		
VOH	$V_I = V_{IH} \text{ or } V_{IL}$		6 V	5.9	5.999		5.9		5.9		
		$I_{OH} = -4 \text{ mA}$	4.5 V	3.98	4.3		3.7		3.84		
		I <sub>OH</sub> = -5.2 mA	6 V	5.48	5.8		5.2		5.34		
	$V_I = V_{IH} \text{ or } V_{IL}$	I <sub>OL</sub> = 20 μA	2 V		0.002	0.1		0.1		0.1	V
			4.5 V		0.001	0.1		0.1		0.1	
VOL			6 V		0.001	0.1		0.1		0.1	
		I <sub>OL</sub> = 4 mA	4.5 V		0.17	0.26		0.4		0.33	
		I <sub>OL</sub> = 5.2 mA	6 V		0.15	0.26		0.4		0.33	
Ц	$V_I = V_{CC} \text{ or } 0$		6 V		±0.1	±100		±1000		±1000	nA
ICC	$V_I = V_{CC} \text{ or } 0,$	IO = 0	6 V			2		40		20	μA
Ci			2 V to 6 V		3	10		10		10	pF

# electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

switching characteristics over recommended operating free-air temperature range,  $C_L = 50 \text{ pF}$  (unless otherwise noted) (see Figure 1)

PARAMETER	FROM TO		Vee	Т	ן = 25°C	;	SN54	HC20	SN74	HC20	UNIT
	(INPUT)	(OUTPUT)	Vcc	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
<sup>t</sup> pd	A, B, C, or D	Y	2 V		45	110		165		140	ns
			4.5 V		14	22		33		28	
			6 V		11	19		28		24	
tţ			2 V		27	75		110		95	
		Y	4.5 V		9	15		22		19	ns
			6 V		7	13		19		16	

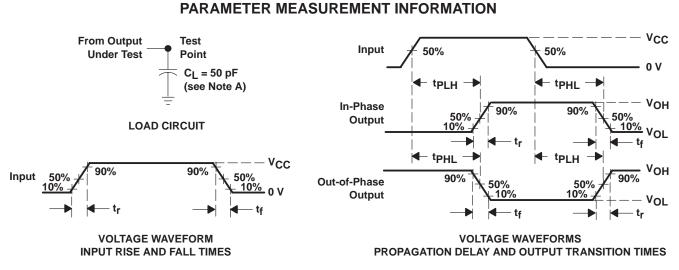
## operating characteristics, $T_A = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	TYP	UNIT
C <sub>pd</sub>	Power dissipation capacitance	No load	25	pF



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- NOTES: A. CL includes probe and test-fixture capacitance.
  - B. Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>f</sub> = 6 ns. t<sub>f</sub> = 6 ns.
  - C. The outputs are measured one at a time with one input transition per measurement.
  - D.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

## Figure 1. Load Circuit and Voltage Waveforms



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